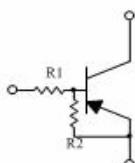



Pb
RoHS
COMPLIANCE

Small Signal Diode

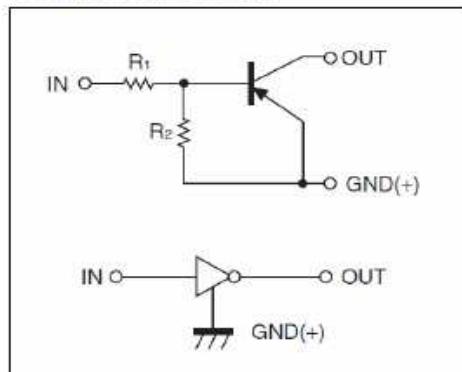


Features

- ◊ Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistor (see equivalent circuit).
- ◊ The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- ◊ Only the on/off conditions need to be set for operation, making device design easy.
- ◊ Green compound (Halogen free) with suffix "G" on packing code and prefix "G" on date code.

DTA114 EM/EE/EUA/ECA/ESA PNP Digital Transistor

• Equivalent Circuit



**SOT-723/SOT-523
SOT-323/SOT-23**

1.IN
2.GND
3.OUT

TO-92S
1.GND
2.OUT
3.IN

Ordering Information

Package	Part No.	Packing	Marking
SOT-723	DTA114 EM	8K / 7" Reel	14
SOT-523	DTA114 EE	3K / 7" Reel	14
SOT-323	DTA114 EUA	3K / 7" Reel	14
SOT-23	DTA114 ECA	3K / 7" Reel	14
TO-92S	DTA114 ESA	3K / 7" Reel	

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Type Number	Symbol	Value					Units
		EM	EE	EUA	ECA	ESA	
Power Dissipation	PD	100	150	200	200	300	mW
Supply Voltage	V _{CC}			-50			V
Input Voltage	V _{IN}			-40~10			V
Output Current	I _O			-50			mA
Peak CollectoCurrent	I _{C(MAX)}			-100			
Junction and Storage Temperature Range	T _J , T _{STG}			-55 to + 150			°C

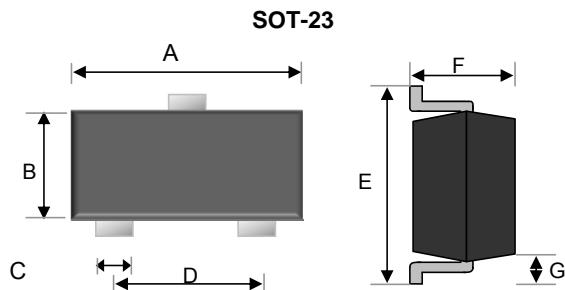
Notes:1. Valid provided that electrodes are kept at ambient temperature

Parameter	Symbol	Min	Typ	Max	Condition	Unit
Input Voltage	V _{I(on)}			-3	V _{CC} =-5V,I _O =-100μA	V
	V _{I(off)}	-0.5			V _O =-0.3V,I _O =-10mA	
Output Voltage	V _{O(on)}			-0.3	I _O /I _I =-10mA/-5mA	V
Input Current	I _I			-0.88	V _I =-5V	mA
Output Current	I _{O (off)}			-0.5	V _{CC} =-50V,V _I =0	μA
DC Current Gain	G _I	30				
Input Resistance	R _I	7	10	13		KΩ
Resistance Ratio	R ₂ /R ₁	0.8	1	1.2		
Transition Frequency	f _T		250		V _O =-10V,I _O =-5mA,f=100MHz	MHz

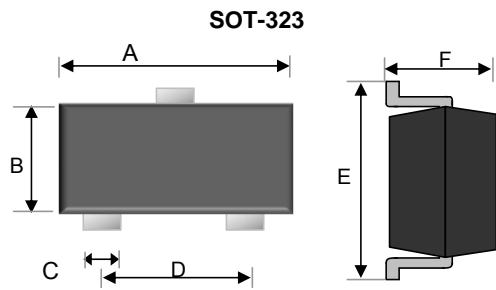


TAIWAN
SEMICONDUCTOR

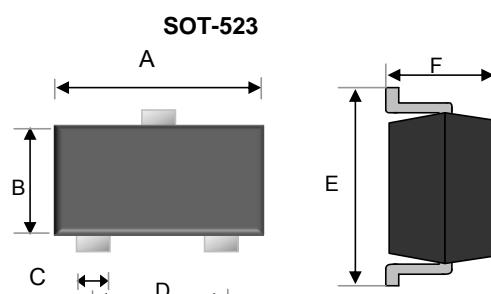
DTA114 EM/EE/EUA/ECA/ESA
PNP Digital Transistor



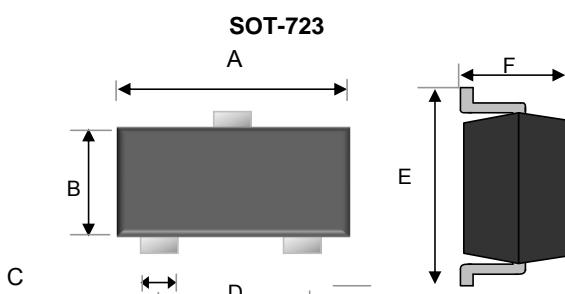
Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	2.80	3.00	0.11	0.12
B	1.20	1.40	0.05	0.06
C	0.30	0.50	0.01	0.02
D	1.80	2.00	0.07	0.08
E	2.25	2.55	0.09	0.10
F	0.90	1.20	0.04	0.04
G	0.550 REF		0.022 REF	



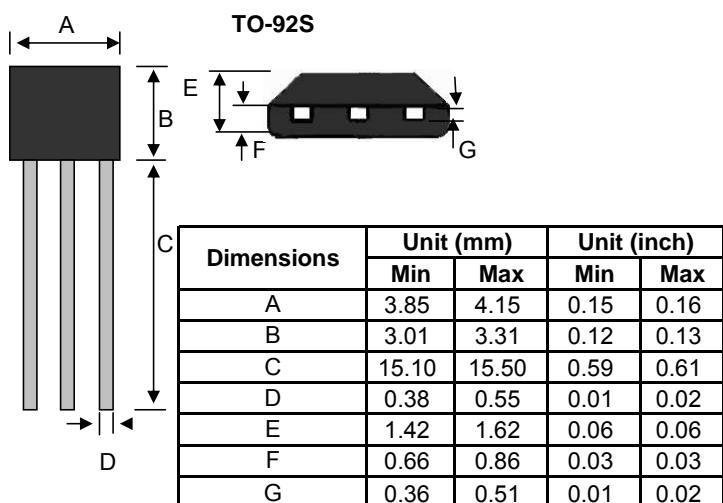
Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.90	2.10	0.07	0.08
B	1.15	1.35	0.05	0.05
C	0.25	0.35	0.01	0.01
D	1.20	1.40	0.05	0.06
E	2.00	2.20	0.08	0.09
F	0.80	1.00	0.03	0.04



Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.50	1.70	0.06	0.07
B	0.70	0.80	0.03	0.03
C	0.25	0.35	0.01	0.01
D	0.90	1.10	0.04	0.04
E	1.50	1.70	0.06	0.07
F	0.70	0.90	0.03	0.04



Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	1.15	1.25	0.05	0.05
B	0.75	0.85	0.03	0.03
C	0.17	0.27	0.01	0.01
D	0.8 TYP		0.31TYP	
E	1.15	1.25	0.05	0.05
F		0.50		0.02



Dimensions	Unit (mm)		Unit (inch)	
	Min	Max	Min	Max
A	3.85	4.15	0.15	0.16
B	3.01	3.31	0.12	0.13
C	15.10	15.50	0.59	0.61
D	0.38	0.55	0.01	0.02
E	1.42	1.62	0.06	0.06
F	0.66	0.86	0.03	0.03
G	0.36	0.51	0.01	0.02